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94401 (US). **HOLLAND, John** [US/US]; 1565 Calaveras Avenue, San Jose, CA 95126 (US).

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(74) Agents: **PATTERSON, B., Todd** et al.; Moser, Patterson & Sheridan, LLP, 3040 Post Oak Boulevard, Suite 1500, Houston, TX 77056-6582 (US).

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(71) Applicant (for all designated States except US): **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, CA 95054 (US).

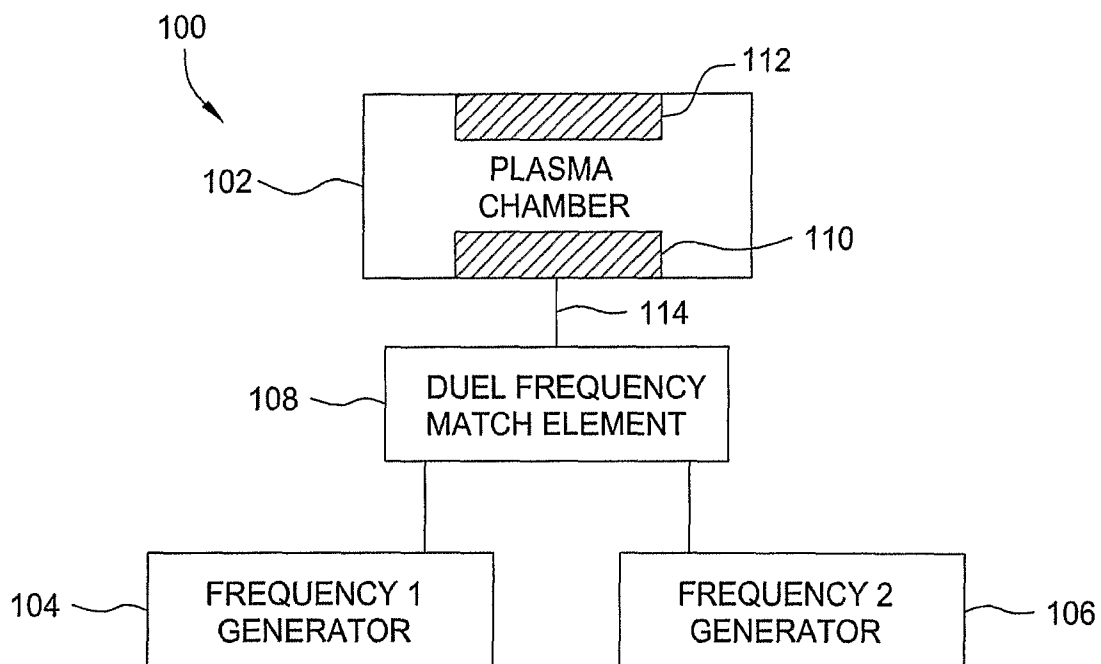
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(72) Inventors; and

(75) Inventors/Applicants (for US only): **SHANNON, Steven, C.** [US/US]; 800 N. Delaware, Apt. 308, San Mateo, CA

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(54) Title: DUAL FREQUENCY RF MATCH



(57) Abstract: A dual frequency matching circuit for plasma enhanced semiconductor processing chambers having dual frequency cathodes is provided. The matching circuit includes two matching circuits with variable shunts combined to a common output. The matching circuit balances the load of the independent RF sources to that of the plasma in the processing chamber during operation.

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